

Attorney Docket No.: 5308-413

PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler et al.

Application No.: 10/849,617

Filed: May 20, 2004

For: **METHODS OF FABRICATING NITRIDE-BASED TRANSISTORS HAVING
REGROWN OHMIC CONTACT REGIONS AND NITRIDE-BASED
TRANSISTORS HAVING REGROWN OHMIC CONTACT REGIONS**

Confirmation No.: 9882

Group Art Unit: 2822

Examiner: Amir Zarabian

Date: June 14, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. § 1.97(b)**

Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the amendment by the U.S. Patent and Trademark Office to 37 C.F.R. § 1.98(a)(2)(ii) effective October 21, 2004. Also enclosed is a translation or a concise explanation of each non-English language document enclosed. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. §1.56 and Section 609 of the MPEP.

This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(b), within three months of the filing date of the above-referenced application or before the mailing of a first Office Action on the merits, whichever event occurs last. Therefore, no fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

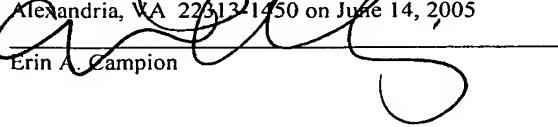

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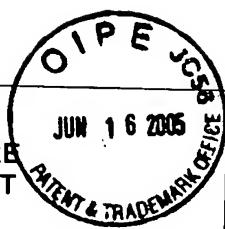
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 3

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|  INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i> | | | | Complete if Known | |
| | | | | Application Number | 10/849,617 |
| | | | | Filing Date | May 20, 2004 |
| | | | | First Named Inventor | Saxler et al. |
| | | | | Group Art Unit | 2822 |
| | | | | Examiner Name | Amir Zarabian |
| | | | | Attorney Docket Number | 5308-413 |
| Sheet | 1 | of | 3 | | |

U.S. PATENTS AND PATENT PUBLICATIONS

FOREIGN PATENT DOCUMENTS

OTHER NON PATENT LITERATURE DOCUMENTS

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|---------------------------------------|----------|--|---|
| Examiner Initials* | Cite No. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published | T |
| | 13. | Ando et al., "10-W/mm AlGaN-GaN HFET With a Field Modulating Plate," <i>IEEE Electron Device Letters</i> , 24(5), pp. 289-291 (May 2003). | |
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*EXAMINER: Initial if reference considered, whether or not citation is:

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| | 40. | United States Patent Application entitled "Aluminum Free Group III-Nitride Based High Electron Mobility Transistors and Methods of Fabricating Same," Serial No. 11/118,575, filed April 29, 2005 (Attorney Docket No. 5308-543). | |
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Examiner Signature

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| | 43. | United States Patent Application entitled "Thick Semi-Insulating or Insulating Epitaxial Gallium Nitride Layers and Devices Incorporating Same," Serial No. 11/103,117, filed April 11, 2005 (Attorney Docket No. 5308-553). | |
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